

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

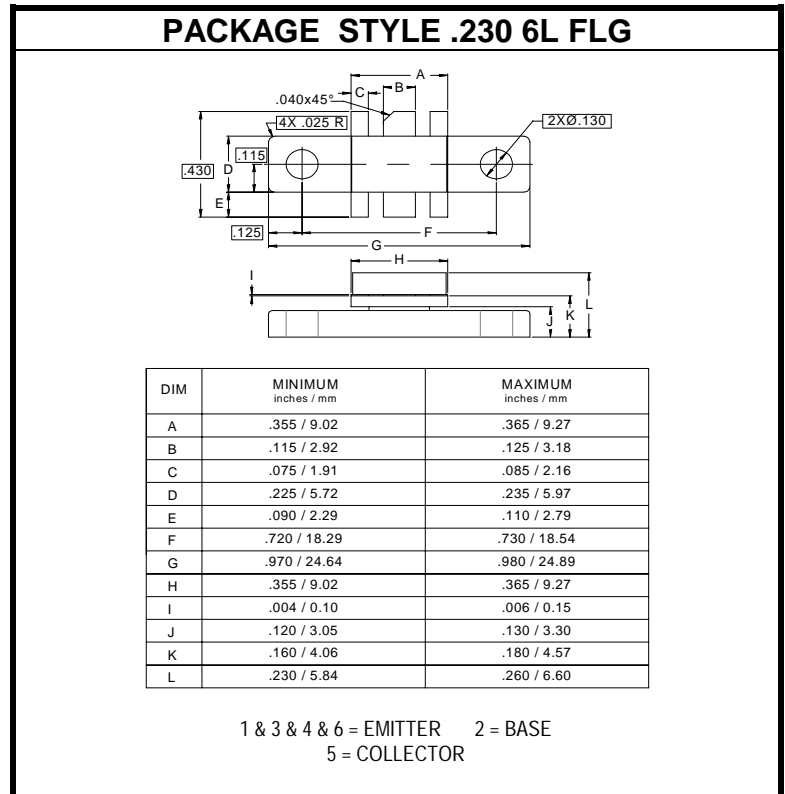
The **MRF839F** is Designed for Class AB, Common Emitter Applications Up to 960 MHz.

FEATURES INCLUDE:

- Input Matching Network
- High Gain
- Gold Metalization

MAXIMUM RATINGS

I_C	0.6 A
V_{CES}	36 V
P_{DISS}	20 W @ T _C = 25 °C
T_J	-55 °C to +200 °C
T_{STG}	-55 °C to +150 °C
θ_{JC}	9.0 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I _C = 5.0 mA	40			V
BV_{CEO}	I _C = 5.0 mA	16			V
BV_{EBO}	I _E = 100 μA	3.5			V
I_{CES}	V _{CE} = 15 V			1	mA
h_{FE}	V _{CE} = 5.0 V I _C = 100 mA	10		150	---
C_{OB}	V _{CB} = 15 V f = 1.0 MHz			10	pF
P_G	V _{CE} = 12.5 V I _{CQ} = 50mA P _{OUT} = 3.0 W	8.0	10.0		dB
η_C	F _O = 870 MHz	50			%